Diode Semiconductor Device - Page 1 of 1



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lr	nclosure Material:
G	Blass and metal
С	overall Length:
0	.340 inches
С	overall Diameter:
0	.187 inches
N	Iounting Facility Quantity:
1	
N	Iounting Method:
Т	hreaded stud
F	eatures Provided:
Н	lermetically sealed case
С	overall Width Across Flats:
0	.187 inches
Т	hread Size:
0	.112 inches
s	emiconductor Material:
S	ilicon
V	oltage Rating In Volts Per Characteristic:
5	0.0 reverse voltage, peak
С	Current Rating Per Characteristic:
1	20.00 amperes average forward current averaged over a full 60-hz cycle
Ρ	ower Rating Per Characteristic:
1	0.0 watts total power dissipation
N	Iaximum Operating Tempurature Per Measurement Point:
1	75.0 degrees celsius ambient air
Т	hread Series Designator:
U	Inc
Т	erminal Type And Quantity:
1	threaded stud and 1 turret
S	helf Life:
N	l/a
U	Init Of Measure:
D	emilitarization:
N	lo
F	iig:
A	110a0